

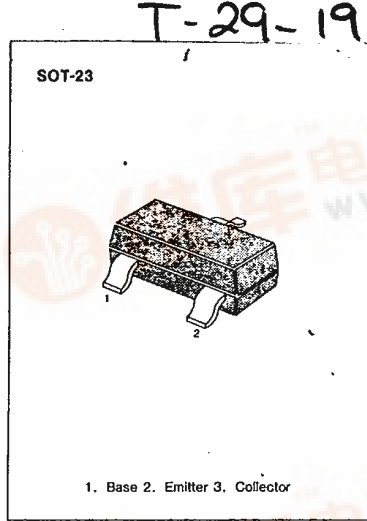
SAMSUNG SEMICONDUCTOR INC 14E D 7964142 0007228 T
MMBA811C5 PNP EPITAXIAL SILICON TRANSISTOR

DRIVER TRANSISTOR

ABSOLUTE MAXIMUM RATINGS (T_a=25°C)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V _{CBO}	50	V
Collector-Emitter Voltage	V _{CEO}	45	V
Emitter-Base Voltage	V _{EBO}	5	V
Collector Current	I _C	50	mA
Collector Dissipation	P _C	350	mW
Storage Temperature	T _{stg}	150	°C

• Refer to MMBT5086 for graphs



ELECTRICAL CHARACTERISTICS (T_a=25°C)

Characteristic	Symbol	Test Condition	Min	Max	Unit
Collector-Base Breakdown Voltage	BV _{CBO}	I _C =100μA, I _E =0	50		V
Collector-Emitter Breakdown Voltage	BV _{CEO}	I _C =1.0mA, I _B =0	45		V
Emitter-Base Breakdown Voltage	BV _{EBO}	I _E =10μA, I _C =0	5		V
Collector Cutoff Current	I _{CBO}	V _{CB} =40V, I _E =0		50	nA
Emitter Cutoff Current	I _{EBO}	V _{EB} =5.0V, I _C =0		50	nA
DC Current Gain	h _{FE}	V _{CE} =3V, I _C =0.1mA	150		
		V _{CE} =3V, I _C =0.5mA	135	270	
Collector-Emitter Saturation Voltage	V _{CE(sat)}	I _C =20mA, I _B =2.0mA		0.3	V
Current Gain-Bandwidth Product	f _T	I _C =1.0mA, V _{CE} =6.0V f=100MHz	75		MHz

Marking

